

# 10V Drive Nch MOSFET

## RSJ400N06

### ● Structure

Silicon N-channel MOSFET

### ● Features

- 1) Low on-resistance.
- 2) High current
- 3) High power Package

### ● Application

Switching

### ● Packaging specifications

| Type      | Package                      | Taping |
|-----------|------------------------------|--------|
|           | Code                         | TL     |
|           | Basic ordering unit (pieces) | 1000   |
| RSJ400N06 |                              | ○      |

### ● Absolute maximum ratings ( $T_a = 25^\circ\text{C}$ )

| Parameter                      |            | Symbol      | Limits      | Unit             |
|--------------------------------|------------|-------------|-------------|------------------|
| Drain-source voltage           |            | $V_{DSS}$   | 60          | V                |
| Gate-source voltage            |            | $V_{GSS}$   | $\pm 20$    | V                |
| Drain current                  | Continuous | $I_D$       | $\pm 40$    | A                |
|                                | Pulsed     | $I_{DP}$ *1 | $\pm 80$    | A                |
| Source current<br>(Body Diode) | Continuous | $I_S$       | 40          | A                |
|                                | Pulsed     | $I_{SP}$ *1 | 80          | A                |
| Power dissipation              |            | $P_D$ *2    | 50          | W                |
| Channel temperature            |            | $T_{ch}$    | 150         | $^\circ\text{C}$ |
| Range of storage temperature   |            | $T_{stg}$   | -55 to +150 | $^\circ\text{C}$ |

\*1  $P_w \leq 10\text{W}$ , Duty cycle  $\leq 1\%$

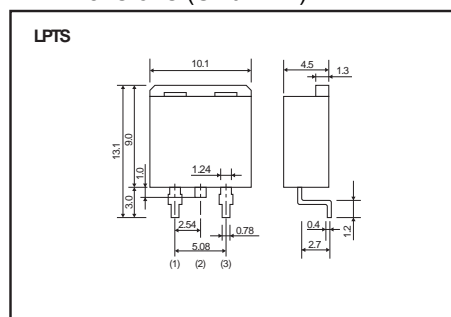
\*2  $T_c = 25^\circ\text{C}$

### ● Thermal resistance

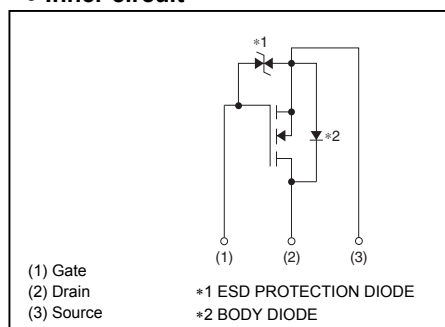
| Parameter       | Symbol           | Limits | Unit                        |
|-----------------|------------------|--------|-----------------------------|
| Channel to Case | $R_{th(ch-c)}$ * | 2.5    | $^\circ\text{C} / \text{W}$ |

\*  $T_c = 25^\circ\text{C}$

### ● Dimensions (Unit : mm)



### ● Inner circuit



●Electrical characteristics (T<sub>a</sub> = 25°C)

| Parameter                               | Symbol                | Min. | Typ. | Max. | Unit | Conditions                                 |
|---|-----------------------|------|------|------|------|--|
| Gate-source leakage                     | I <sub>GSS</sub>      | -    | -    | ±10  | μA   | V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V |
| Drain-source breakdown voltage          | V <sub>(BR)DSS</sub>  | 60   | -    | -    | V    | I <sub>D</sub> =1mA, V <sub>GS</sub> =0V   |
| Zero gate voltage drain current         | I <sub>DSS</sub>      | -    | -    | 1    | μA   | V <sub>DS</sub> =60V, V <sub>GS</sub> =0V  |
| Gate threshold voltage                  | V <sub>GS(th)</sub>   | 1.0  | -    | 3.0  | V    | V <sub>DS</sub> =10V, I <sub>D</sub> =1mA  |
| Static drain-source on-state resistance | R <sub>DS(on)</sub> * | -    | 11   | 16   | mΩ   | I <sub>D</sub> =40A, V <sub>GS</sub> =10V  |
| Forward transfer admittance             | Y <sub>fs</sub>   *   | 14   | -    | -    | S    | I <sub>D</sub> =20A, V <sub>DS</sub> =10V  |
| Input capacitance                       | C <sub>iss</sub>      | -    | 2400 | -    | pF   | V <sub>DS</sub> =10V                       |
| Output capacitance                      | C <sub>oss</sub>      | -    | 490  | -    | pF   | V <sub>GS</sub> =0V                        |
| Reverse transfer capacitance            | C <sub>rss</sub>      | -    | 250  | -    | pF   | f=1MHz                                     |
| Turn-on delay time                      | t <sub>d(on)</sub> *  | -    | 20   | -    | ns   | I <sub>D</sub> =20A, V <sub>DD</sub> ≒ 30V |
| Rise time                               | t <sub>r</sub> *      | -    | 60   | -    | ns   | V <sub>GS</sub> =10V                       |
| Turn-off delay time                     | t <sub>d(off)</sub> * | -    | 90   | -    | ns   | R <sub>L</sub> =1.5Ω                       |
| Fall time                               | t <sub>f</sub> *      | -    | 140  | -    | ns   | R <sub>G</sub> =10Ω                        |
| Total gate charge                       | Q <sub>g</sub> *      | -    | 52   | -    | nC   | V <sub>DD</sub> ≒ 30V                      |
| Gate-source charge                      | Q <sub>gs</sub> *     | -    | 8    | -    | nC   | I <sub>D</sub> =40A,                       |
| Gate-drain charge                       | Q <sub>gd</sub> *     | -    | 15   | -    | nC   | V <sub>GS</sub> =10V                       |

\*Pulsed

●Body diode characteristics (Source-Drain) (T<sub>a</sub> = 25°C)

| Parameter       | Symbol            | Min. | Typ. | Max. | Unit | Conditions                               |
|-----------------|-------------------|------|------|------|------|--|
| Forward Voltage | V <sub>SD</sub> * | -    | -    | 1.2  | V    | I <sub>s</sub> =40A, V <sub>GS</sub> =0V |

\*Pulsed

●Electrical characteristic curves (Ta=25°C)

Fig.1 Static Drain-Source On-State Resistance vs. Drain Current

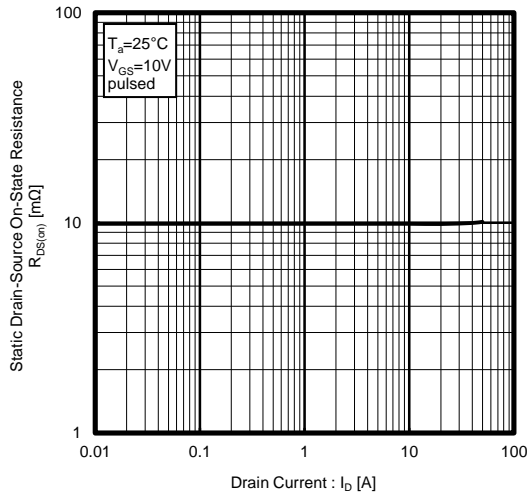


Fig.2 Static Drain-Source On-State Resistance vs. Drain Current

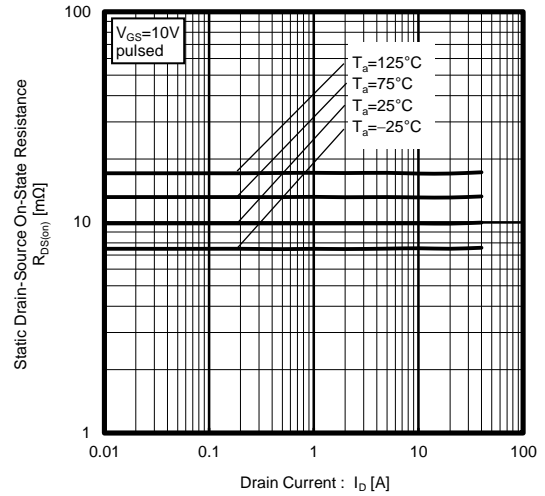


Fig.3 Static Drain-Source On-State Resistance vs. Drain Current

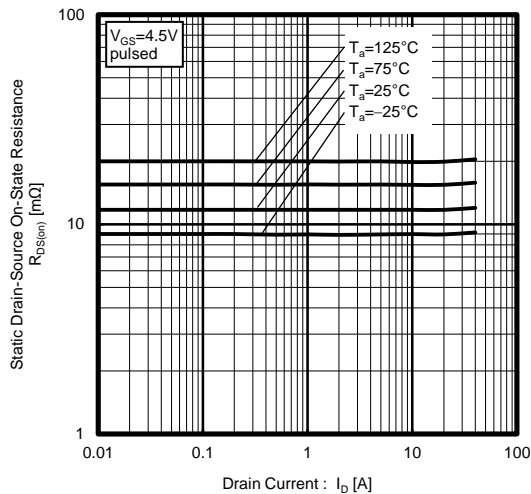


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current

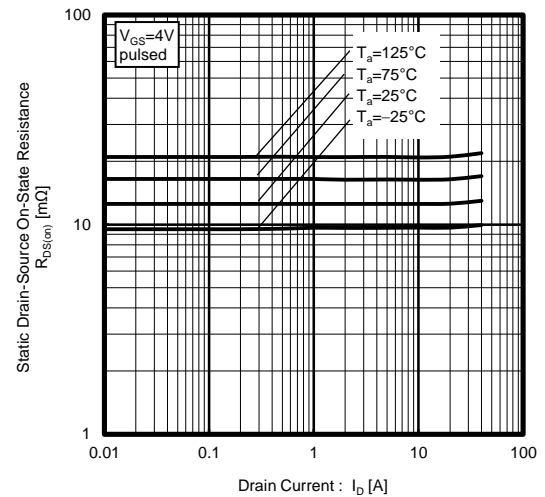


Fig.5 Forward Transfer Admittance vs. Drain Current

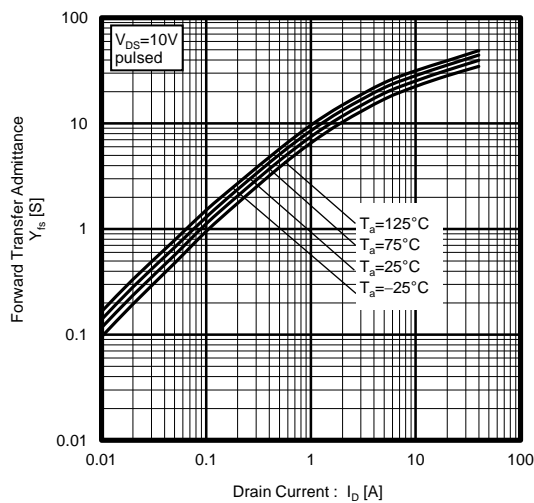


Fig.6 Typical Transfer Characteristics

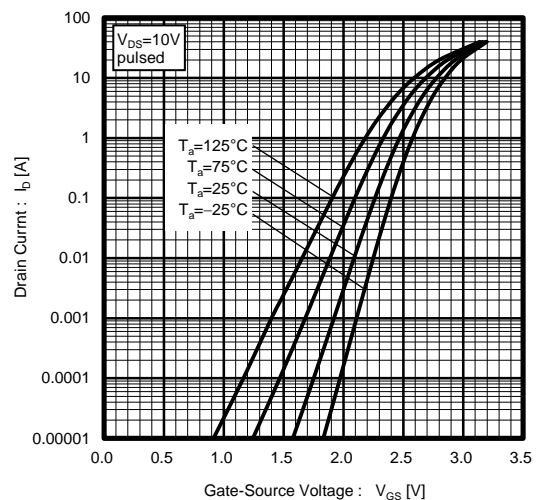


Fig.7 Source Current vs. Source-Drain Voltage

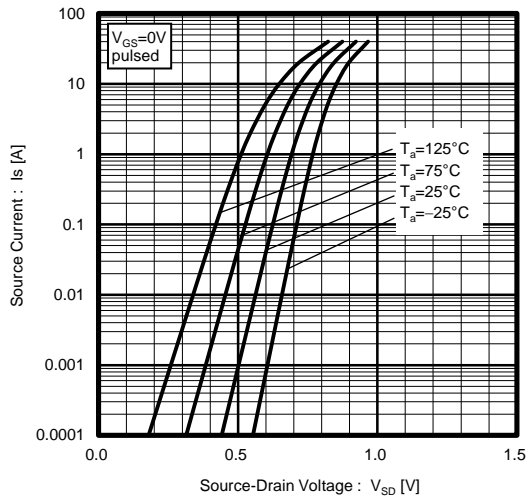


Fig.8 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

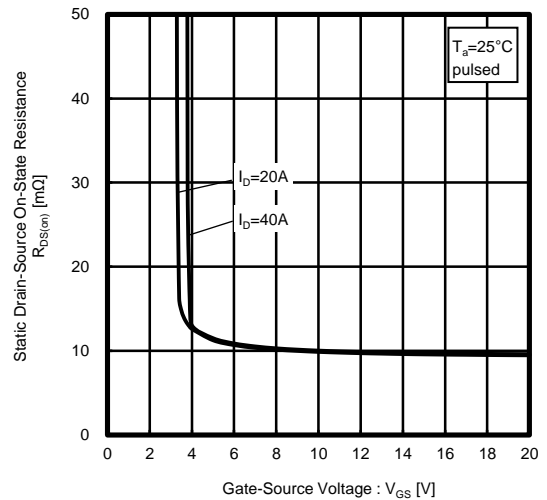


Fig.9 Switching Characteristics

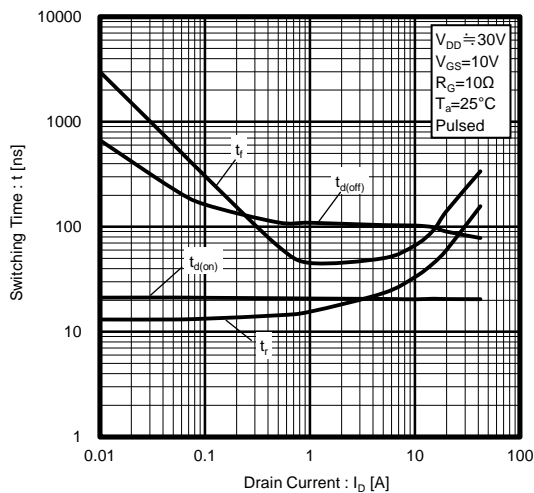


Fig.10 Dynamic Input Characteristics

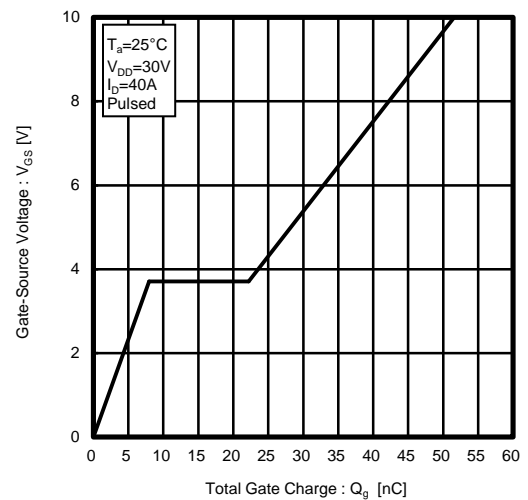


Fig.11 Typical Capacitance vs. Drain-Source Voltage

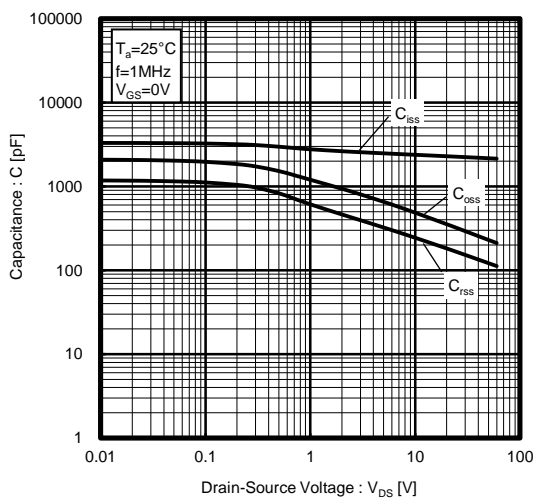
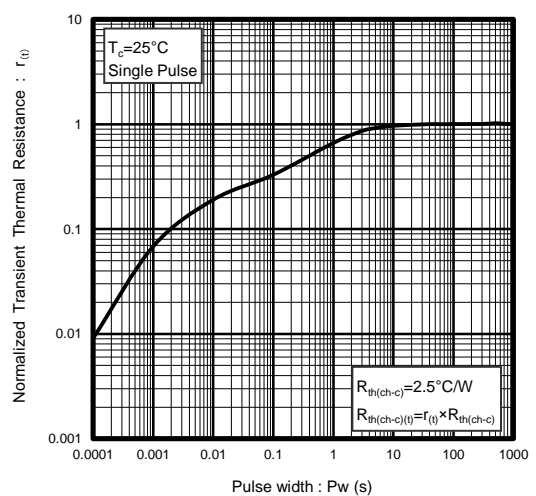


Fig.12 Normalized Transient Thermal Resistance v.s. Pulse Width



## ● Measurement circuits

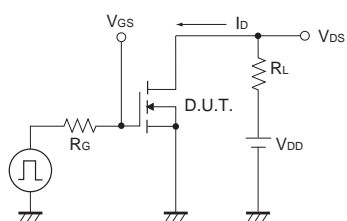


Fig.1-1 Switching Time Measurement Circuit

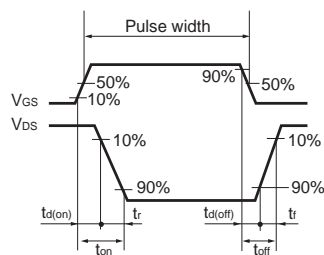


Fig.1-2 Switching Waveforms

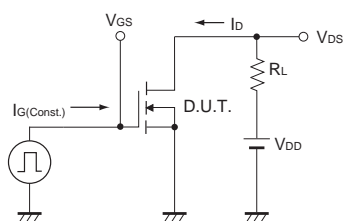


Fig.2-1 Gate Charge Measurement Circuit

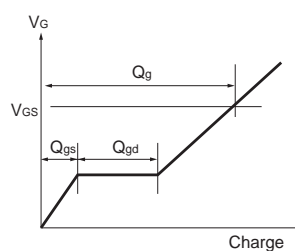


Fig.2-2 Gate Charge Waveform

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